In the Claims:

Please cancel claims 21-91.

Please amend claims 1-3, 6, 7 and 10-14 as shown in the Replacement Claims.

Replacement Claims

1. (Amended) A method for etching an oxide layer of a substrate, comprising:

placing a substrate having an oxide layer formed over said substrate into a reactive chamber;

introducing into said chamber an etching gas;

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generating a plasma of said etching gas at a first power level and contacting said oxide layer of said substrate with said first power level plasma for a first predetermined time; and,

generating a plasma of said etching gas at a second power level in said chamber and contacting said oxide layer of said substrate with said second power level plasma for a second predetermined time to etch said oxide layer, wherein said first and second power levels are different.

2. (Amended) The method according to claim 1, wherein said first power level is from about 100 Watts to about 250 Watts.

3. (Amended) The method according to claim 1, wherein said first power level is about 150 Watts.

6. (Amended) The method according to claim 1, wherein said second power level is from about 800 Watts to about 1100 Watts.

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7. (Amended) The method according to claim 1, wherein said second power level is about 950 Watts.

10. (Amended) The method according to claim 1, wherein said first power level and said second power level plasmas of said etching gas are selected from the group consisting of Cl_2, HBr, CF_4, CHF_3, CH_2F_2 and inert gases.

11. (Amended) The method according to claim 10, wherein said first power level plasma is CF_4, CHF_3 and an inert gas.

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12. (Amended) The method according to claim 10, wherein said second power level plasma is CF_4, CHF_3 and an inert gas.

13. (Amended) The method according to claim 10, wherein said first power level and said second power level plasmas are CF_4, CHF_3 and Ar.

14. (Amended) The method according to claim 10, wherein said first power level and said second power level plasmas are CF_4, CHF_3 and He.